

**GaAs Flip Chip  
Schottky Barrier Diodes**

**MA4E1317, MA4E1318,  
MA4E1319-1, MA4E1319-2 V1**

**Features**

- Low Series Resistance
- Low Capacitance
- High Cutoff Frequency
- Silicon Nitride Passivation
- Polyimide Scratch Protection
- Designed for Easy Circuit Insertion

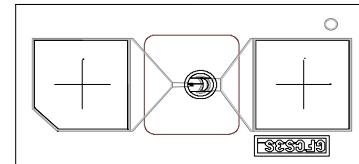
**Description and Applications**

M/A-COM's MA4E1317 single, MA4E1318 anti-parallel pair, MA4E1319-1 reverse tee and MA4E1319-2 series tee are gallium arsenide flip chip Schottky barrier diodes. These devices are fabricated on OMCVD epitaxial wafers using a process designed for high device uniformity and extremely low parasitics. The diodes are fully passivated with silicon nitride and have an additional layer of polyimide for scratch protection. The protective coatings prevent damage to the junction during automated or manual handling. The flip chip configuration is suitable for pick and place insertion.

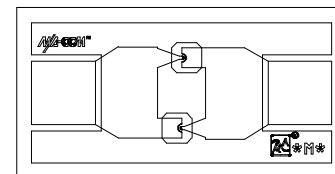
The high cutoff frequency of these diodes allows use through millimeter wave frequencies. Typical applications include single and double balanced mixers in PCN transceivers and radios, police radar detectors, and automotive radar detectors. The devices can be used through 80 GHz.

The MA4E1318 anti-parallel pair is designed for use in subharmonically pumped mixers. Close matching of the diode characteristics results in high LO suppression at the RF input.

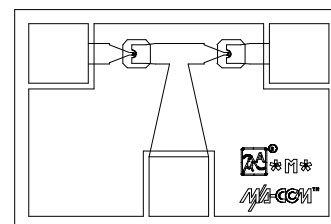
**MA4E1317**



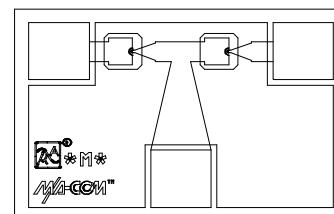
**MA4E1318**



**MA4E1319-1**



**MA4E1319-2**



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**Electrical Specifications @ Ta = 25 °C**

Parameters and Test Conditions	Symbol	Units	MA4E1317			MA4E1318			MA4E1319-1 or -2		
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max
Junction Capacitance at 0V at 1 Mhz	Cj	pF		.020			.020 <sup>3</sup>			.020 <sup>3</sup>	
Total Capacitance at 0V at 1 Mhz <sup>1</sup>	Ct	pF	.030	.045	.060	.030 <sup>3</sup>	.045 <sup>3</sup>	.060 <sup>3</sup>	.030 <sup>3</sup>	.045 <sup>3</sup>	.060 <sup>3</sup>
Junction Capacitance Difference	ΔCj	pF					.005	.010		.005	.010
Series Resistance at +10mA <sup>2</sup>	Rs	Ohms		4	7		4	7		4	7
Forward Voltage at +1mA	Vf1	Volts	.60	.70	.80	.60	.70	.80	.60	.70	.80
Forward Voltage Difference at 1mA	ΔVf	Volts					.005	.010		.005	.010
Reverse Breakdown Voltage at -10uA	Vbr	Volts	4.5	7					4.5	7	
SSB Noise Figure	NF	dB		6.5 <sup>4</sup>			6.5 <sup>4</sup>			6.5 <sup>4</sup>	

**Notes:**

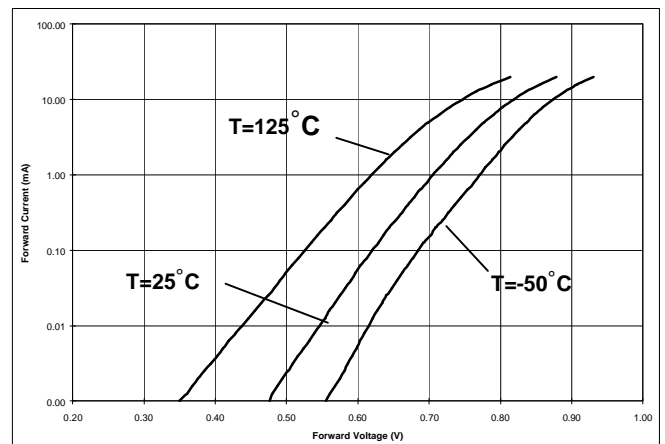
- Total capacitance is equivalent to the sum of junction capacitance Cj and parasitic capacitance Cp.
- Series resistance is determined by measuring the dynamic resistance and subtracting the junction resistance of 2.6 ohms.
- Capacitance for the MA4E1318 and MA4E1319-1 or -2 is per Schottky diode.
- Measured at an LO frequency of 9.375 Ghz, with an IF frequency of 300 Mhz. LO drive level is +6 dBm for a single Schottky junction. The IF noise figure contribution (1.5 dB) is included.

**Absolute Maximum Ratings @ 25 °C  
(Unless Otherwise Noted)<sup>1</sup>**

Parameter	Absolute Maximum
Operating Temperature	-65 °C to +125 °C
Storage Temperature	-65 °C to +150 °C
Junction Temperature	+175 °C
Incident LO Power	+ 20 dBm
Incident RF Power	+ 20 dBm
Mounting Temperature	+235 °C for 10 seconds

- Operation of this device above any one of these parameters may cause permanent damage.

**Forward Current vs Temperature**



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### Mounting Techniques

These chips were designed to be inserted onto hard or soft substrates with the junction side down. They can be mounted with conductive epoxy or with a low temperature solder preform. The die can also be assembled with the junction side up, and wire or ribbon bonds made to the pads.

**Solder Die Attach:** Solders with < 30% Sn by volume or weight are recommended. 80 Au / 20 Sn and Indalloy #2 solders are recommended. Do not expose die to a temperature greater than 235°C, or greater than 200°C for longer than 10 seconds. No more than three seconds of scrubbing should be required for attachment.

**Conductive epoxy Die Attach:** Assembly can be preheated to 125 - 150°C. Use a controlled amount of epoxy approximately 2 mils thick. Cure epoxy as per manufacturer's schedule. For extended cure times, temperatures should be kept below 200°C.

### Handling

The following precautions should be observed to avoid damaging these chips:

**Cleanliness:** These chips should be handled in a clean environment. Do not attempt to clean die after installation.

**Static Sensitivity:** Schottky barrier diodes are ESD sensitive and can be damaged by static electricity. Proper ESD techniques should be used when handling these devices.

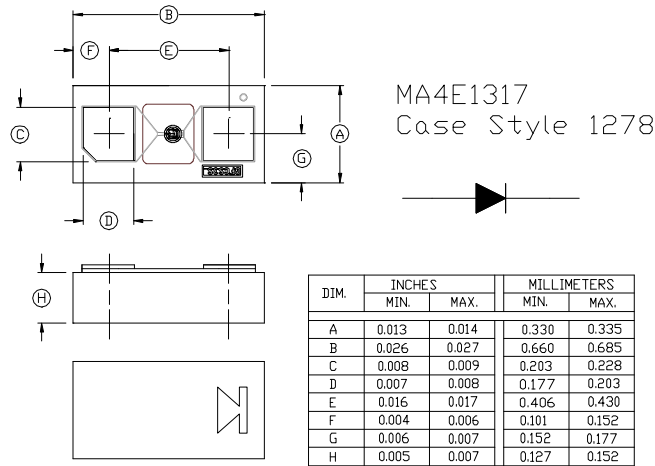
**General Handling:** The protective polymer coating on the active areas of these die provides scratch protection, particularly for the metal airbridge which contacts the anode. Die can be handled with tweezers or vacuum pickups and are suitable for use with automatic pick-and-place equipment.

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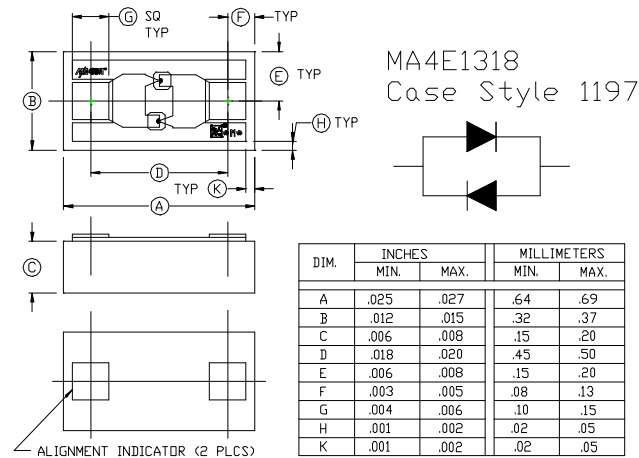
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**Chip Outline Drawings**

**MA4E1317  
Case Style 1278**



**MA4E1318  
Case Style 1197**

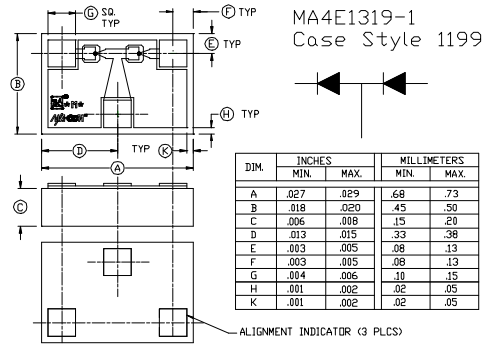


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**Chip Outline Drawings**

**MA4E1319-1  
Case Style 1199**



**MA4E1319-2  
Case Style 1200**

